

# AP50P03K

## P-Channel Power MOSFET

### ● General Description

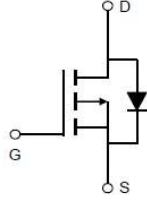
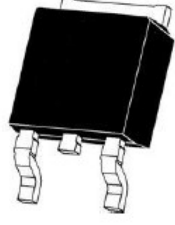
The AP50P03K combines advanced trench MOSFET technology with a low resistance package to provide extremely low  $R_{DS(ON)}$ . This device is ideal for load switch and battery protection applications.

### ● Features

- Advance high cell density Trench technology
- Low  $R_{DS(ON)}$  to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

### ● Application

- MB/VGA Vcore
- SMPS 2<sup>nd</sup> Synchronous Rectifier
- POL application
- BLDC Motor driver

	$V_{DS} = -30V$  $R_{DS(ON)} = 15m\Omega$  $I_D = -35A$
 <p><b>TO-252-2L top view</b></p>	

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AP50P03	AP50P03K	TO-252-2L	-	-	-

### ● Absolute Maximum Ratings ( $T_c = 25^\circ C$ )

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current ( $T_C = 25^\circ C$ )	$I_D$	-35	A
Pulsed Drain Current <sup>①</sup>	$I_{DM}$	-70	A
Total Power Dissipation <sup>②</sup>	$P_D @ T_C = 25^\circ C$	40	W
Total Power Dissipation	$P_D @ T_A = 25^\circ C$	0.9	W
Operating Junction Temperature	$T_J$	-55 to 150	$^\circ C$
Storage Temperature	$T_{STG}$	-55 to 150	$^\circ C$
Single Pulse Avalanche Energy	$E_{AS}$	100	mJ

**AP50P03K**
**P-Channel Power MOSFET**
**•Thermal resistance**

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case <sup>②</sup>	R <sub>thJC</sub>	-	-	34	° C/W
Thermal resistance, junction - ambient	R <sub>thJA</sub>	-	-	180	° C/W
Soldering temperature, wavesoldering for 10s	T <sub>sold</sub>	-	-	265	° C

**•Electronic Characteristics**

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250uA	-30			V
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = -250uA	-1.2		-2.5	V
Drain-Source Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V			-1.0	uA
Gate- Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±12V, V <sub>DS</sub> = 0V			±100	nA
Static Drain-source On Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = -10V, I <sub>D</sub> = -9A		15	20	mΩ
		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -8A		25	32	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = -10V, I <sub>D</sub> = -5A		9		s

**•Electronic Characteristics**

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C <sub>iss</sub>	f = 1MHz	-	1650	-	pF
Output capacitance	C <sub>oss</sub>		-	330	-	
Reverse transfer capacitance	C <sub>rss</sub>		-	220	-	

**•Gate Charge characteristics(T<sub>a</sub> = 25°C)**

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q <sub>g</sub>	V <sub>DD</sub> = 25V I <sub>D</sub> = 8A V <sub>GS</sub> = 10V	-	15	-	nC
Gate - Source charge	Q <sub>gs</sub>		-	4	-	
Gate - Drain charge	Q <sub>gd</sub>		-	6	-	

Note: ① Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2% ;

② Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate;

**AP50P03K**  
**P-Channel Power MOSFET**

Fig.1 Power Dissipation Derating Curve

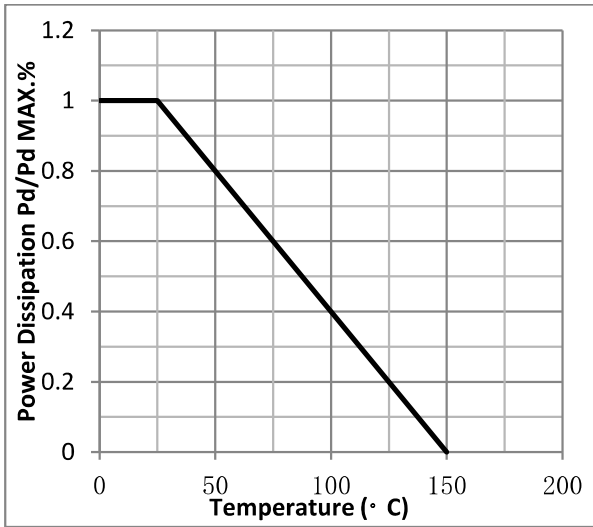


Fig.2 Typical output Characteristics

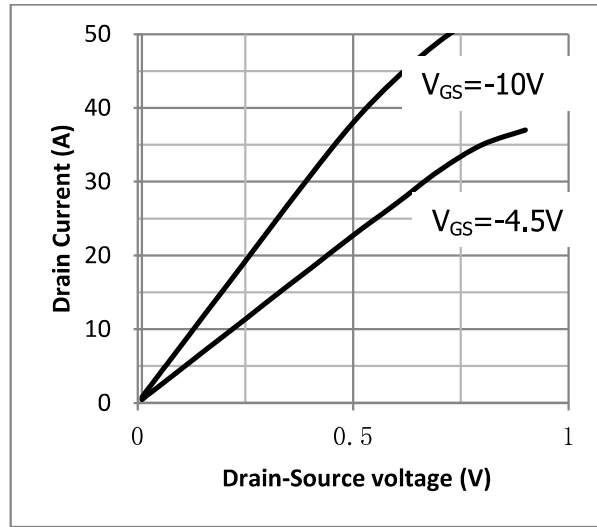


Fig.3 Threshold Voltage V.S Junction Temperature

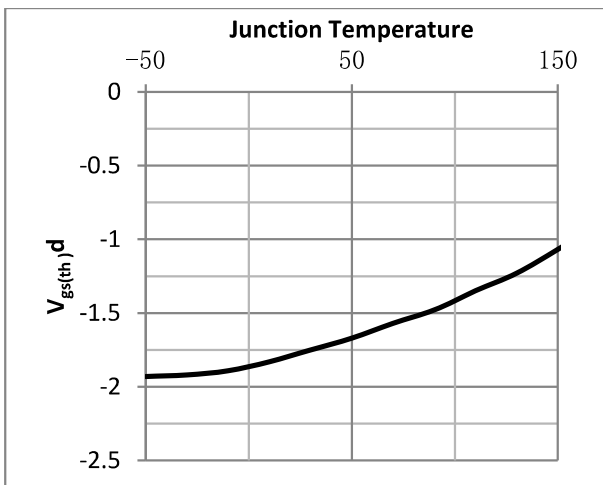


Fig.4 Resistance V.S Drain Current

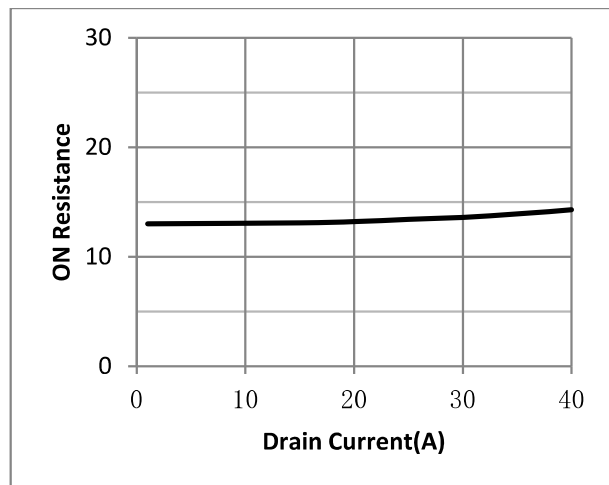


Fig.5 On-Resistance VS Gate Source Voltage

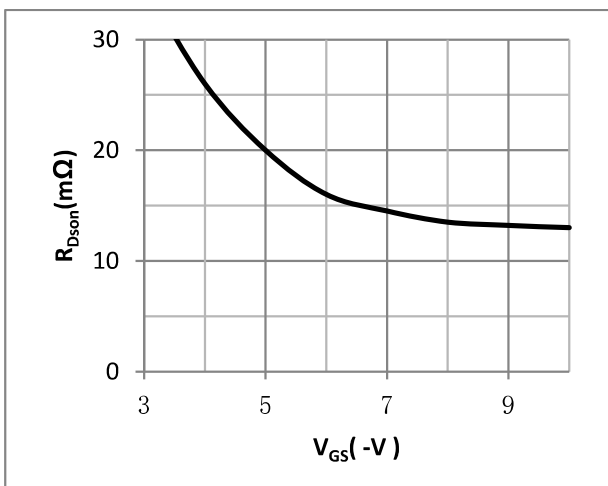
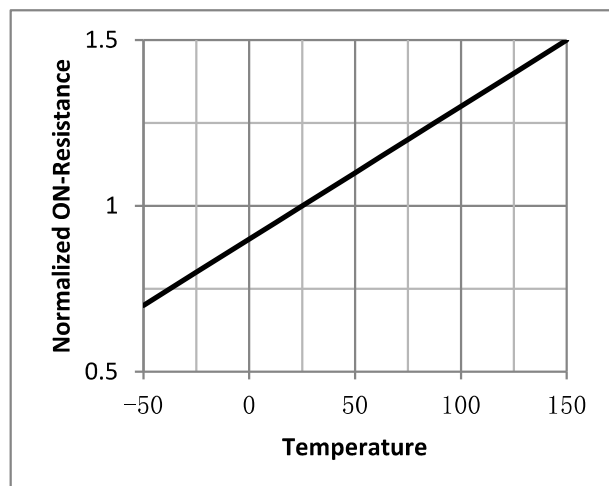


Fig.6 On-Resistance V.S Junction Temperature



**AP50P03K**

**P-Channel Power MOSFET**

Fig.7 Switching Time Measurement Circuit

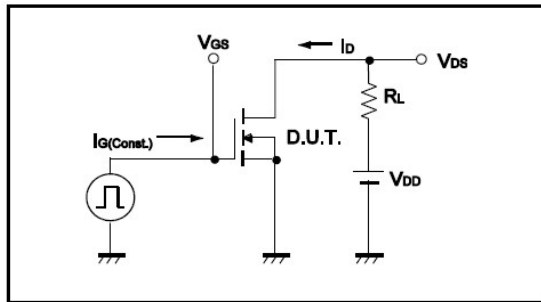


Fig.8 Gate Charge Waveform

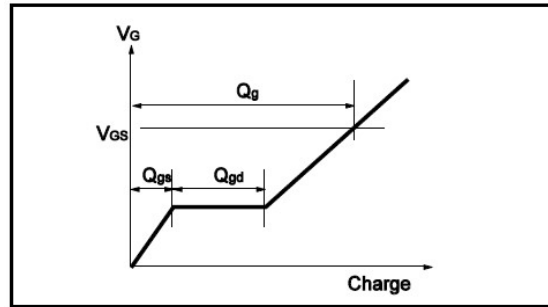


Fig.9 Switching Time Measurement Circuit

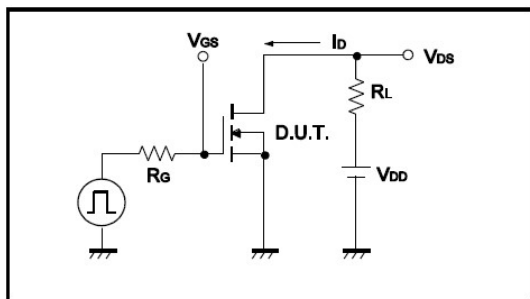


Fig.10 Gate Charge Waveform

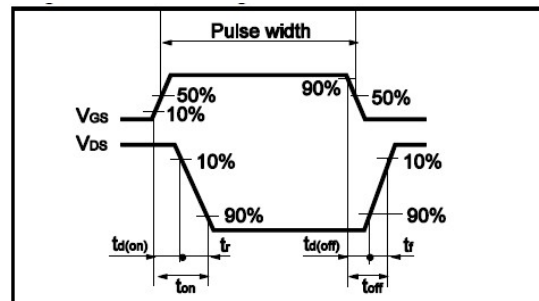


Fig.11 Avalanche Measurement Circuit

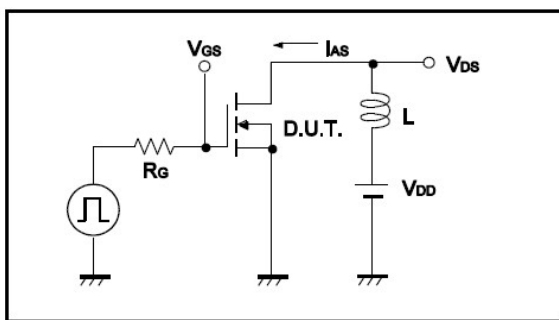
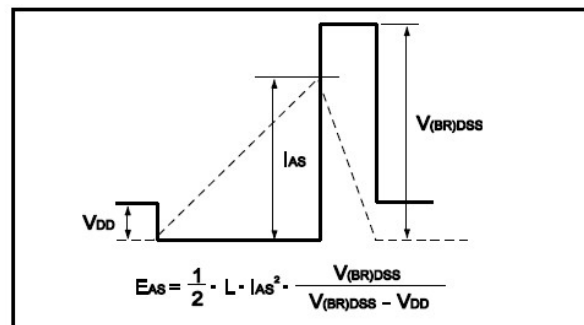


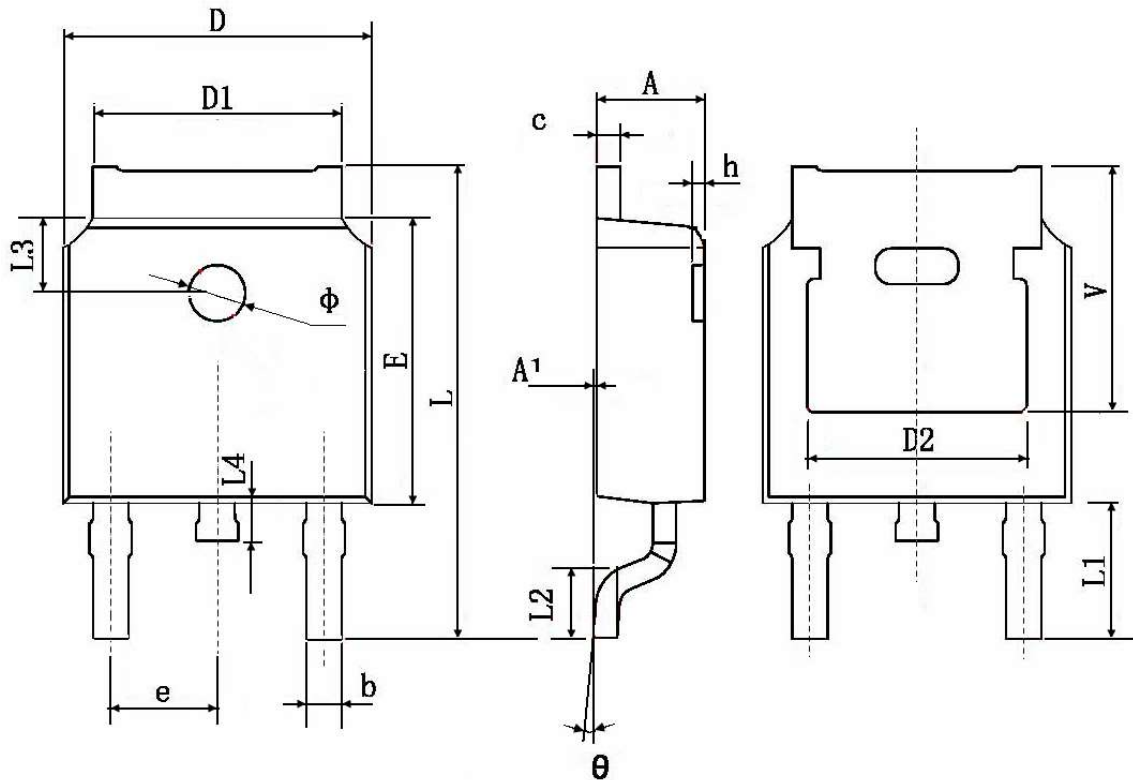
Fig.12 Avalanche Waveform



**AP50P03K**

**P-Channel Power MOSFET**

**TO-252 Package Information**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	